

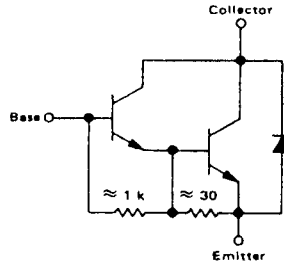


NPN SILICON POWER DARLINGTON TRANSISTORS

The MJ10012 is a high voltage, high-current darlington transistor designed for automotive ignition, switching regulator and motor control applications.

FEATURES:

- *Continuous Collector Current - $I_C = 10\text{ A}$
- *Collector-Emitter Sustaining Voltage-
 $V_{CEO(SUS)} = 400\text{V (Min)}$
- *Automotive Function Tests

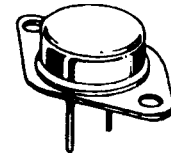


**NPN
MJ10012**

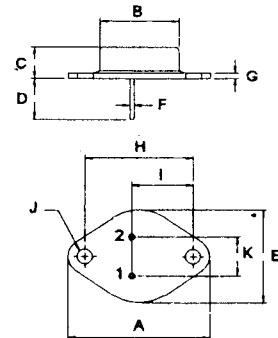
**10 AMPERE
POWER DARLINGTON
TRANSISTORS
400 VOLTS
175 WATTS**

MAXIMUM RATINGS

Characteristic	Symbol	MJ10012	Unit
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage ($R_{BE} = 27\Omega$)	V_{CER}	550	V
Collector-Emitter Voltage	$V_{CEO(SUS)}$	400	V
Emitter-Base Voltage	V_{EBO}	8.0	V
Collector Current-Continuous	I_C	10	A
-Peak	I_{CM}	15	
Base current	I_B	2	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	175	W
Derate above 25°C		100	W
		1.0	W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +200	$^\circ\text{C}$



TO-3

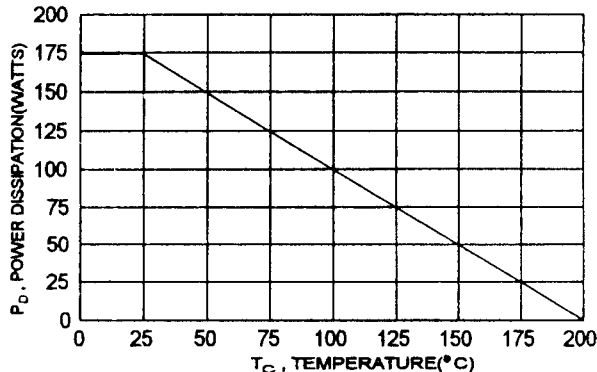


PIN 1.BASE
2.EMITTER
COLLECTOR(CASE)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.0	$^\circ\text{C/W}$

FIGURE -1 POWER DERATING



DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage ($I_C = 200\text{ mA}, I_B = 0, V_{\text{clamp}} = \text{Rate } V_{\text{CEO}}$)	$V_{\text{CEO(sus)}}$	400		V
Collector - Emitter Sustaining Voltage ($I_C = 200\text{ mA}, I_B = 0, R_{\text{BE}} = 27\text{ ohm}, V_{\text{clamp}} = \text{Rate } V_{\text{CER}}$)	$V_{\text{CER(sus)}}$	425		V
Collector Cutoff Current (Rated $V_{\text{CER}}, R_{\text{BE}} = 27\text{ ohm}$)	I_{CER}		1.0	mA
Collector Cutoff Current (Rated $V_{\text{CBO}}, I_E = 0$)	I_{CBO}		1.0	mA
Emitter Cutoff Current ($V_{\text{EB}} = 6.0\text{ V}, I_C = 0$)	I_{EBO}		40	mA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 3.0\text{ A}, V_{\text{CE}} = 6.0\text{ V}$) ($I_C = 6.0\text{ A}, V_{\text{CE}} = 6.0\text{ V}$) ($I_C = 10\text{ A}, V_{\text{CE}} = 6.0\text{ V}$)	hFE	300 100 20	2000	
Collector - Emitter Saturation Voltage ($I_C = 3.0\text{ A}, I_B = 300\text{ mA}$) ($I_C = 6.0\text{ A}, I_B = 600\text{ mA}$) ($I_C = 10\text{ A}, I_B = 2.0\text{ A}$)	$V_{\text{CE(sat)}}$		1.5 2.0 2.5	V
Base - Emitter Saturation Voltage ($I_C = 6.0\text{ A}, I_B = 600\text{ mA}$) ($I_C = 10\text{ A}, I_B = 2.0\text{ A}$)	$V_{\text{BE(sat)}}$		2.5 3.0	V
Base - Emitter On Voltage ($I_C = 10\text{ A}, V_{\text{CE}} = 6.0\text{ V}$)	$V_{\text{BE(on)}}$		2.8	V
Diode Forward Voltage ($I_F = 10\text{ A}$)	V_F		3.5	V

DYNAMIC CHARACTERISTICS

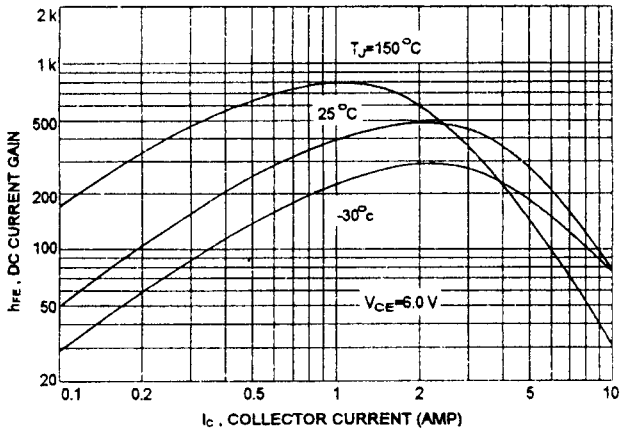
Output Capacitance ($V_{\text{CB}} = 10\text{ V}, I_E = 0, f = 100\text{ kHz}$)	C_{ob}		350	pF
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SWITCHING CHARACTERISTICS

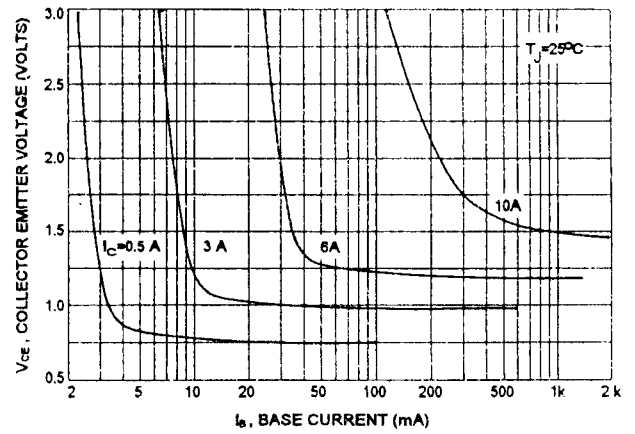
Storage Time	$V_{\text{CC}} = 12\text{ V}, I_C = 6.0\text{ A}$ $I_{\text{B1}} = -I_{\text{B2}} = 0.3\text{ A}$ $t_p = 25\text{ us}, \text{Duty Cycle} \leq 2\%$	t_s	15	us
Fall Time		t_f	15	us

(1) Pulse Test: Pulse width = 300 us , Duty Cycle $\leq 2.0\%$

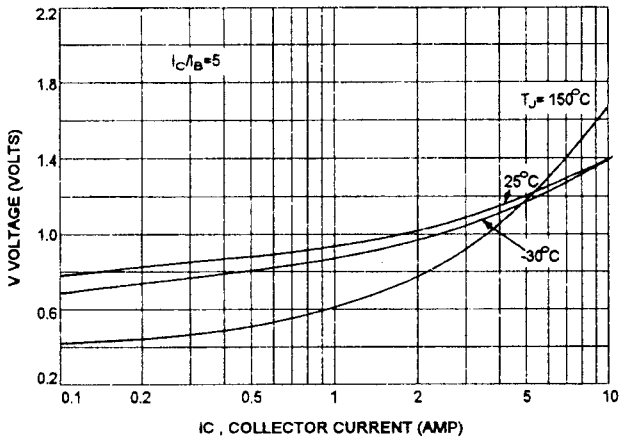
DC CURRENT GAIN



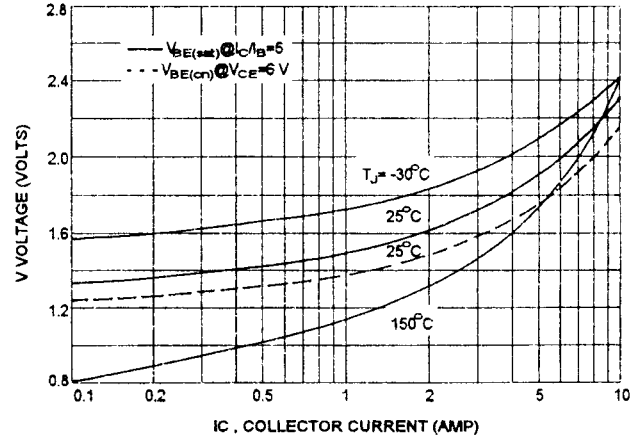
COLLECTOR SATURATION REGION



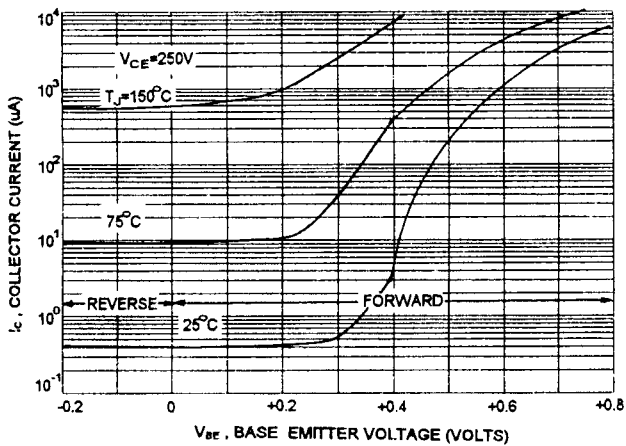
COLLECTOR-EMITTER SATURATION VOLTAGE



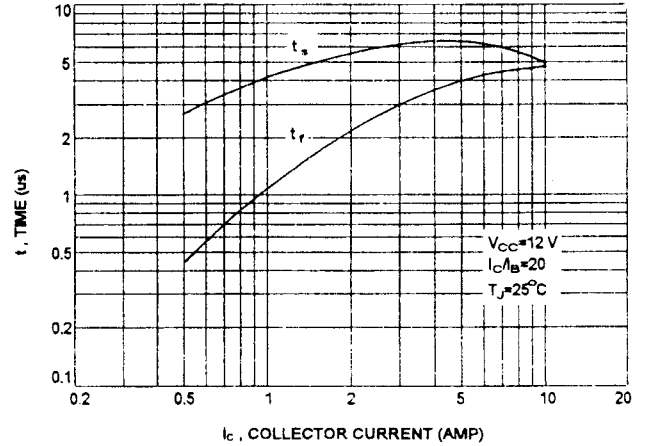
BASE-EMITTER VOLTAGE



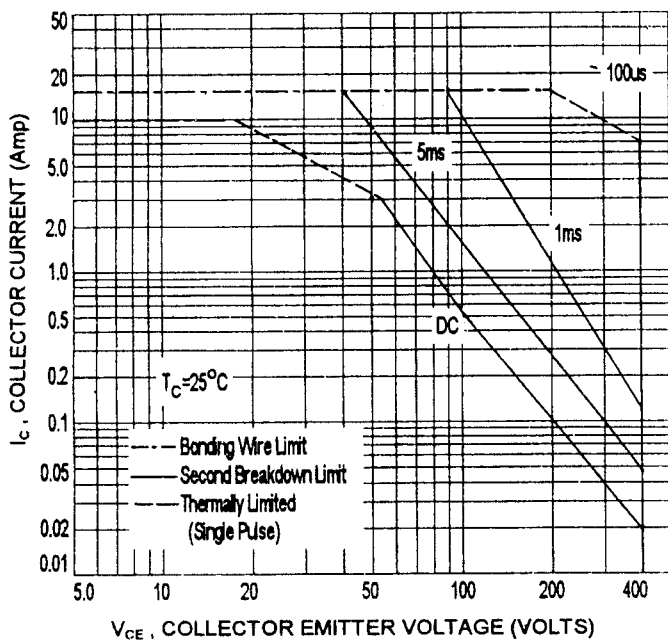
COLLECTOR CUT-OFF REGION



TURN-OFF TIME



ACTIVE-REGION SAFE OPERATING AREA (SOA)



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_c - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curves is base on $T_{J(PK)} = 200^\circ\text{C}$; T_c is variable depending on conditions. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.